

Description

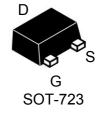
The HRUM002N02T2L uses advanced trench technology

to provide excellent $R_{DS(ON)}$, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



General Features

 $V_{DS} = 20V I_{D} = 1.2A$

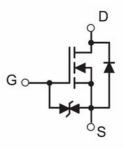
$$\begin{split} &R_{DS(ON)} < 260 \text{ m}\Omega @ \text{ V}_{GS} = 4.5\text{V} \\ &R_{DS(ON)} < 350 \text{ m}\Omega @ \text{ V}_{GS} = 2.5\text{V} \\ &ESD \text{ Rating: } 1500\text{V HBM} \end{split}$$

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HRUM002N02T2L	SOT-723	HXY MOSFET	8000

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Continuous Drain Current	I _D	1.2	А
Pulsed Drain Current	I _{DM}	1.8	А
Power Dissipation	P _D	0.15	W
Thermal Resistance from Junction to Ambient	R _{θJA}	833	°C/W
Junction Temperature	TJ	150	$^{\circ}$
Storage Temperature	Tstg	-55~ +150	$^{\circ}$

N-Channel Enhancement Mode MOSFET

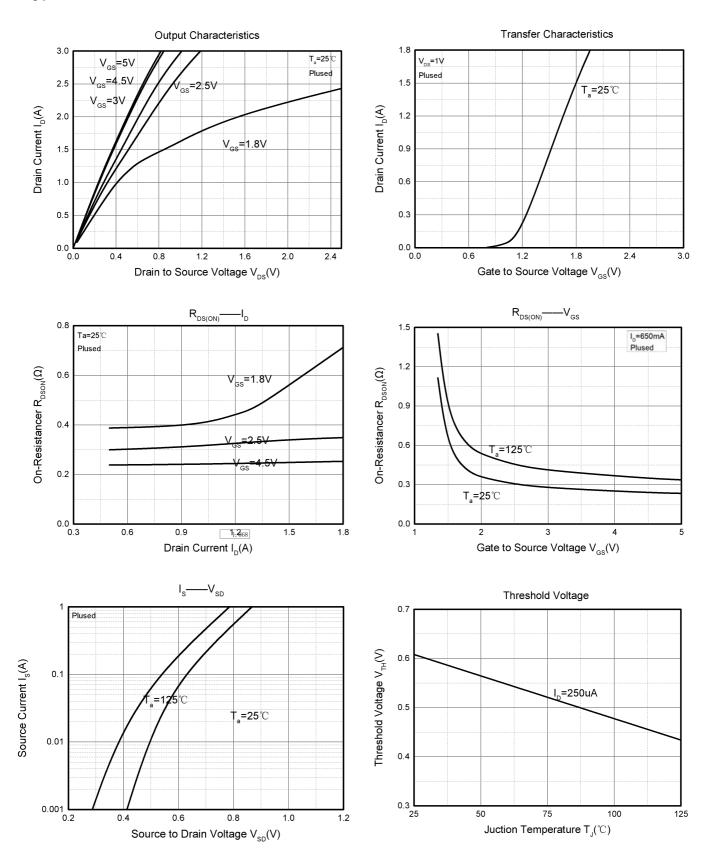
Electrical characteristics (T_A=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =16V,V _{GS} = 0V			1	μΑ
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±10	uA
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.3	0.65	1	٧
	R _{DS(on)}	V _{GS} = 4.5V, I _D = 1.2A		150	260	mΩ
Drain-source on-resistance		V _{GS} =2.5V, I _D = 0.8A		132	168	
		V _{GS} =1.8V, I _D = 0.3A		165	240	
Input Capacitance	C _{iss}			79	120	pF
Output Capacitance	Coss	V _{DS} =16V,V _{GS} =0V, f=1MHz		13	20	
Reverse Transfer Capacitance	C _{rss}	1 111112		9	15	
Turn-on delay time	t _{d(on)}			6.7		
Turn-on rise time	t _r	V _{GS} =4.5V,V _{DS} =10V,		4.8		ns
Turn-off delay time	t _{d(off)}	$I_D = 500 \text{mA}, R_{GEN} = 10\Omega$		17.3		
Turn-off fall time	t _f			7.4		
Body Diode Voltage	V _{SD}	I _S =0.5A, V _{GS} = 0V		0.7	1.3	V



N-Channel Enhancement Mode MOSFET

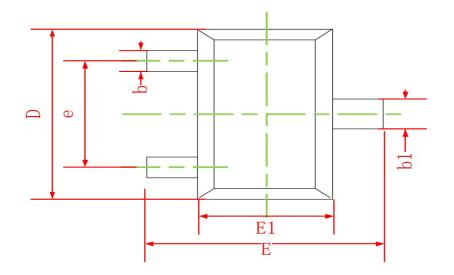
Typical Characteristics

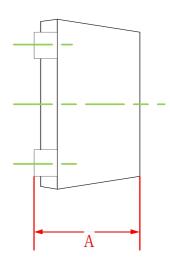


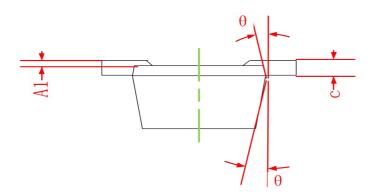


N-Channel Enhancement Mode MOSFET

SOT-723 Package Information







	Dimensions In Millimeters			
Symbol	Min.	Max.		
A	0.430	0.500		
A1	0.000	0.050		
b	0.170	0.270		
b1	0.270	0.370		
С	0.080	0.150		
D	1.150 1.250			
E	1.150 1.250			
E1	0.750 0.850			
е	0.800TYP.			
θ	7° REF.			



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